



VDRM

T(AV)

Iтsм dV/dt*

dl/dt

KEY PARAMETERS

8500V

740A

9800A

1500V/µs

200A/µs

*Higher dV/dt selections are available on request

DCR750F85

Replaces DS5934-6

DS5934-7 April 2024 (LN43248)

Phase Control Thyristor

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- Medium Voltage Soft Starts
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages Vdrm and Vrrm (V)	Conditions
		$T_{vj} = -40^{\circ}C$ to $125^{\circ}C$,
DCR750F85*	8500	Idrm = Irrm = 200mA,
DCR750F80	8000	Vdrm, Vrrm tp = 10ms
DCR750F75	7500	Vdsm & Vrsm =
DCR750F70	7000	Vdrm & Vrrm + 100V
		respectively

Lower voltage grades available.

*8200V @ -40°C, 8500V @ 0°C

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR750F85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

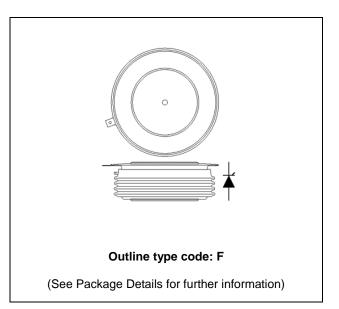


Fig. 1 Package outline

www.dynexsemi.com

CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter Test Conditions		Max.	Units
Double Si	de Cooled			
Ιτ(Αν)	Mean on-state current	Half wave resistive load	740	А
It(rms)	RMS value	-	1160	А
lτ	Continuous (direct) on-state current	-	1150	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, Tcase = 125°C	9.8	kA
l²t	I ² t for fusing	VR = 0	0.48	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditior	Min.	Max.	Units	
		Double side cooled	DC	-	18.3	°C/kW
Rth(j-c)	Thermal resistance - junction to case		Anode DC	-	33.3	°C/kW
		Single side cooled	Cathode DC	-	41.7	°C/kW
Rth(c-h) Thermal	Thermal registeres ages to besteink	Clamping force 23kN (with mounting compound)	Double side	-	4.0	°C/kW
	Thermal resistance - case to heatsink		Single side	-	8.0	°C/kW
Tvj	Virtual junction temperature	Blocking VDRM / VRRM		-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force		20	25	kN	

DYNAMIC CHARACTERISTICS

Symbol	Parameter Test Conditions		Min.	Max.	Units	
Irrm/Idrm	Peak reverse and off-state current	At Vrrm/Vdrm, Tcase = 125°C		-	200	mA
Vтм	Instantaneous forward voltage	At 2900A peak, Tj = 25°C		3.65	4.30	V
dV/dt	Max. linear rate of rise of off-state voltage	То 67% Vdrм, Tj = 125°С, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% VDRM to 2x $I_{T(AV)}$ Gate source 30V, 10 Ω	Repetitive 50Hz	-	100	A/µs
		tr < 0.5µs, Tj = 125°C	Non-repetitive	-	200	A/µs
	Threshold voltage - Low level	100A to 500A at T _{case} = 12	5°C	-	1.03	V
V τ(το)	Threshold voltage - High level	500A to 2500A at T _{case} = 125°C		-	1.30	V
-	On-state slope resistance - Low level	100A to 500A at T _{case} = 125°C		-	2.08	mΩ
ľτ	On-state slope resistance - High level	500A to 2500A at T _{case} = 125°C			1.55	mΩ
tgd	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10 Ω tr = 0.5µs, Tj = 25°C		-	3	μs
tq	Turn-off time	Tj = 125°C, Ipeak = 1000A, tp = 1000µs, VR = 100V, dI/dt = 5A/µs, dVpR/dt = 20V/µs linear to 2500V		-	1200	μs
Qs	Stored charge	Iτ = 1000A, tp = 1000μs, Tj =	= 125°C,	3000	4000	μC
IRR	Reverse recovery current dl/dt = 5A/µs, V _{R peak} = 1		/. [LEM]	95	118	А
Qs	Stored charge	$T_j = 125^{\circ}C$, dl/dt = 1A/µs,		(Typ.) 3160		μC
Irr	Reverse recovery current	VR peak ~ 4400V, VR ~ 2600V		(Тур).) 40	А
L	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
Ін	Holding current	Tj = 25°C, R _G -к = ∞, Iтм = 50	0A, I⊤ = 5A	-	300	mA

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GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Vgt	Gate trigger voltage	VDRM = 5V, Tcase = 25°C	1.5	V
Vgd	Gate non-trigger voltage	At 50% Vdrm, Tcase = 125°C	0.4	V
Іст	Gate trigger current	Vdrm = 5V, Tcase = 25°C	350	mA
Igd	Gate non-trigger current	At 50% Vdrm, Tcase = 125°C	10	mA

CURVES

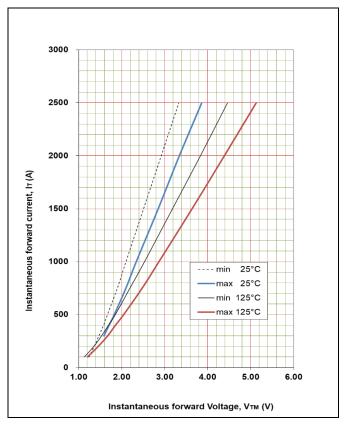


Fig. 2 Maximum & minimum on state characteristics

VTM EQUATION

$$V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$$

Where A = 0.263791B = 0.175445C = 0.001404D = -0.000328These values are valid for T_j = 125° C for I_T 100A to 2500A

-180

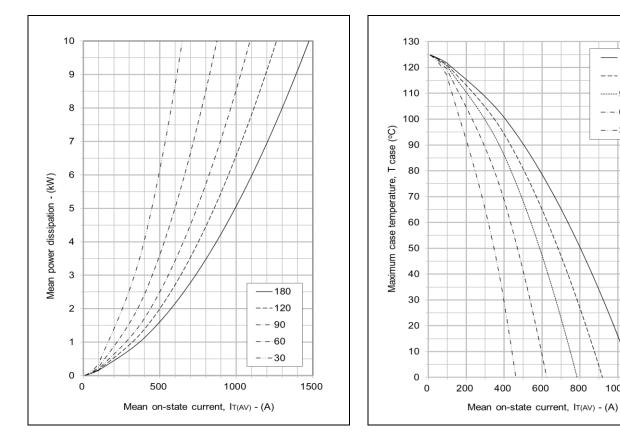
---120

----- 90

--- 60

1000

1200



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Fig. 3 On-state power dissipation - sine wave

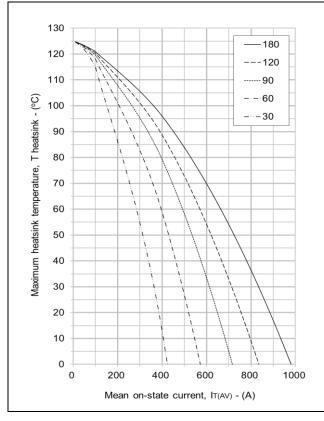


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

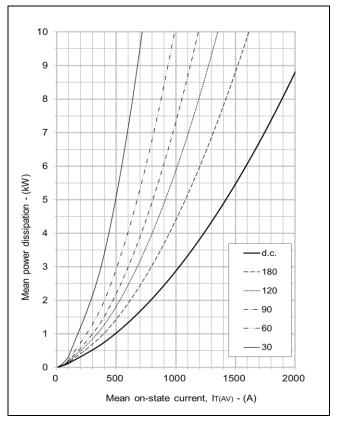


Fig. 6 On-state power dissipation - rectangular wave

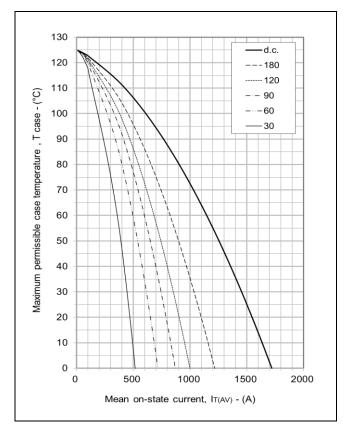
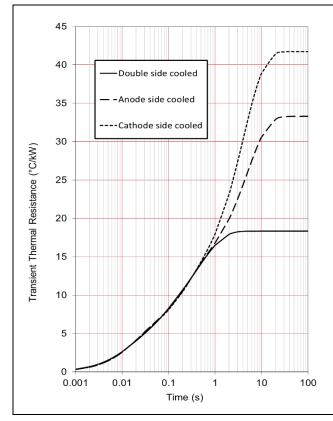


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



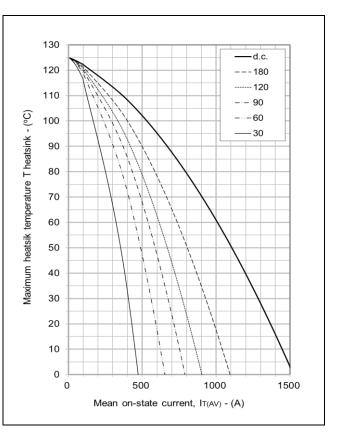


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	7.561	4.077	3.842	2.867
cooled	Ti(s)	0.688	0.254	0.061	0.010
Anode side cooled	Ri(°C/kW)	11.556	8.581	4.794	8.364
	Ti(s)	4.222	6.027	0.017	0.226
Cathode side	Ri(°C/kW)	6.721	4.622	15.539	14.863
cooled	Ti(s)	0.191	0.016	5.001	3.317

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

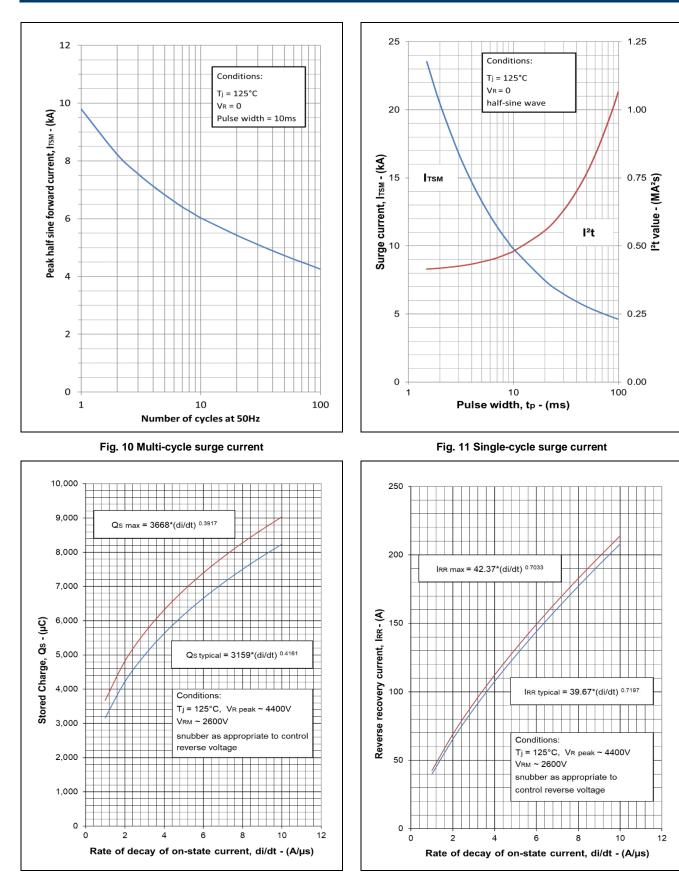
∆R_{th(j-c)} Conduction

Tables show the increments of thermal resistance R $_{\text{fr}(j-q)}$ when the device operates at conduction angles other than d.c.

	Double side cooling		Double side cooling Anode Side Cooling				Ca	Cathode Sided Cooling		
	$\Delta Z_{th}(z)$			$\Delta Z_{th}(z)$			∆Z,	_{th} (z)		
θ°	sine.	rect.	θ°	sine.	rect.	θ°	sine.	rect.		
180	3.19	2.14	180	2.97	2.03	180	295	2.02		
120	3.72	3.10	120	3.43	289	120	3.40	2.87		
90	4.29	3.64	90	3.92	3.36	90	3.88	3.34		
60	4.81	4.23	60	4.36	3.87	60	4.31	3.84		
30	5.22	4.88	30	4.69	4.41	30	4.64	4.37		
15	5.40	5.22	15	4.84	4.70	15	4.79	4.65		



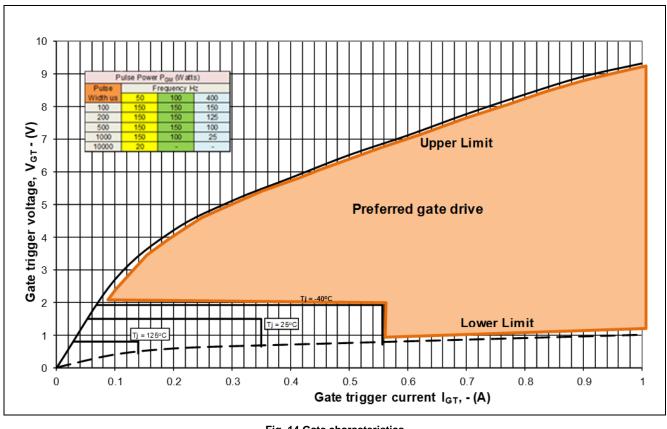
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Fig. 12 Stored charge

Fig. 13 Reverse recovery current



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Fig. 14 Gate characteristics

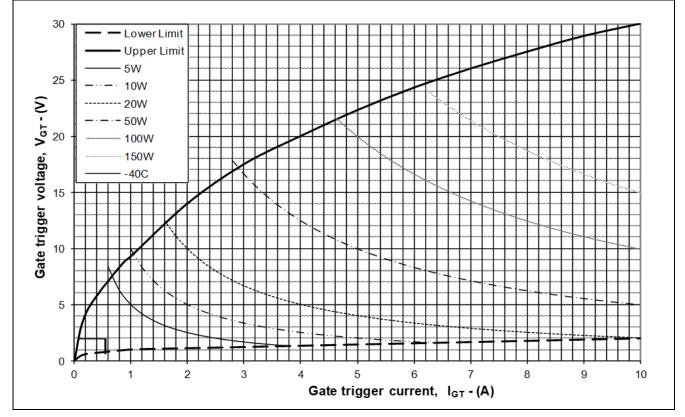
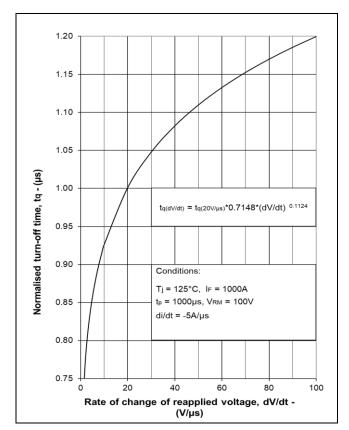


Fig. 15 Gate characteristics



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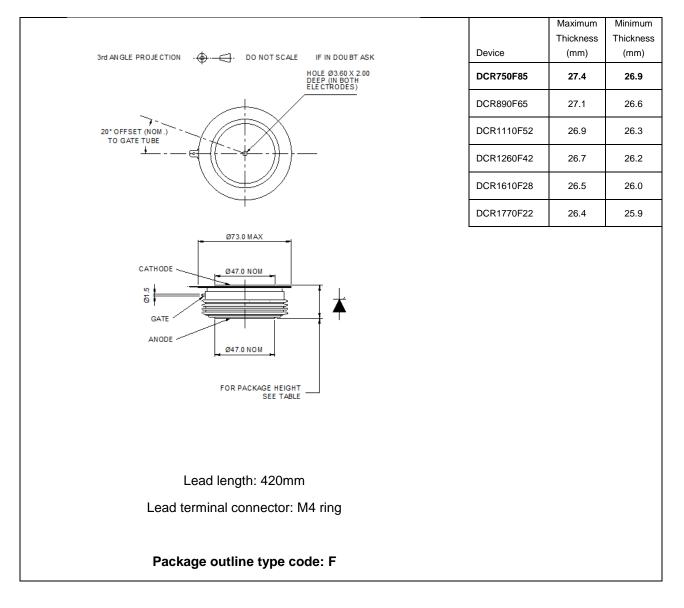
Fig. 16 Turn-off time

PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE



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Fig. 17 Package outline

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